

ams NanEyeM

Datasheet

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NanEyeM Miniature camera module

1 General description

NanEyeM is a miniature sized image sensor for vision applications where size is a critical factor. The ability of the camera head to drive a signal through long cables makes this the ideal component for minimal diameter endoscopes.

With a footprint of a just 1 mm², it features a 320x320 resolution with a high sensitive 2.4 - micron rolling shutter pixel, with large full well capacitance. The sensor has been specially designed for medical endoscopic applications where high SNR is mandatory. The sensor has a high frame rate of about 49 fps to permit SNR enhancement and a smooth, low delay display over a wide range of standard interfaces. On the other side the frame rate can be set as low as 4 fps for usage of extended exposure time and lower power consumption.

The sensor includes a 10-bit ADC and a bit serial LVDS data interface. The sensor is able to drive the signal through a cable length of up to 3 m.

The data line is semi duplex, such that configuration can be communicated to the sensor in the frame brake. The exposure time, dark level, analog gain and frame rate can be programmed over the serial configuration interface.

1.1 Key specifications

Table 1: Key specifications of NanEyeM

Parameter	Value	Remark
Resolution	102.4 kP, 320 (H) x 320 (V)	
Pixel size	2.4 µm x 2.4 µm	
Optical format	1/15"	
Pixel type	4T shared, FSI	
Shutter type	Rolling Shutter	
Color filters	RGB (Bayer Pattern)	
Micro lenses	Yes	
Lens stack	BF = 8 mm DOF = 4 mm to infinite EFL = 367 µm	Triple element lens
Programmable register	Sensor parameter	Exposure time, dark level, frame rate, analog gain and LVDS drive current

Parameter	Value	Remark
Programmable gain	4 steps 0.8x/1x/1.3x/2x	Analog
Exposure times	0.13 – 261 ms	@ Default main clock
ADC	10-bit	Column ADC
Frame rate	4-38 fps (5-49 fps HS mode)	Adjustable via register settings
Output interface	1x LVDS @ 63 Mbps	@ 49 Hz
Size	1050 μm x 1050 μm ±60 μm	Module including sensor, lens stack, side wall painting and cable assembly

1.2 Key benefits & features

The benefits and features of NanEyeM, Miniature camera module are listed below:

Table 2: Added value of using NanEyeM

Benefits	Features
Compact size design for applications with strict size restrictions	Footprint of 1mm² with cable assembly
Adjustable frame rate	Frame rate of 4-49 fps @ 320x320 resolution
High end optics offering reduced distortion and improved MTF, having sharp and accurate image	Integrated wafer level multi element high end performance optics
Envision the unseen	102.4k pixel resolution using 2.4μm highly sensitive pixel, with reduced noise and higher light efficiency by increased resolution
Designed with focus on cost efficiency	All-in-one cost-optimized complete camera module solution including optics & cable for easy integration, being ideal for single-use application. Pre-assembled cable eliminates the complexities of cable procurement and attachment.
Digital Interface	Possible to drive a signal through an endoscope of up to 3 m with low EMI

1.3 Electro-optical characteristics

Table 3: Electro-optical parameters⁽¹⁾⁽²⁾

Parameter	RGB	Unit
Responsivity	8.9	DN/nJ/cm²
Full well capacity	6.2	ke-
Conversion gain	0.137	DN/e-
QE	42.5	%
Temporal read noise in dark / dark noise	0.84 6.1	DN e-
Dynamic range	60	dB
SNR (50% sat)	34	dB
SNR max	38.4	dB
Dark current @ 60 °C	9.2	DN/s
DSNU	0.84	DN
PRNU	1.3	%
FSD	860	DN

- (1) Measured on a RGB sensor at 530 nm illumination, for MCLK=25 MHz setting. The values are all without software correction. The measurement methods used to get these values are those recommended by the European Machine Vision Association standard 1288 for the Machine Vision Sensors and Cameras: [EMVA 1288](#)
- (2) The values show in the table are averaged values across several samples and different operating points (supply, clock speed, gain, etc).

Figure 1: QE & responsivity (RGB)

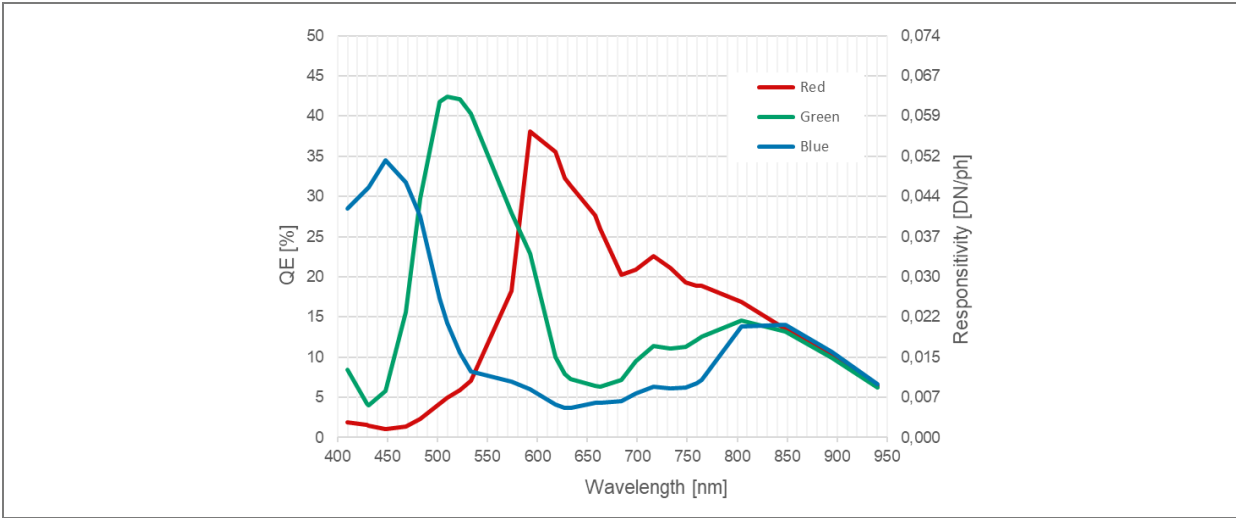


Figure 2: MTF

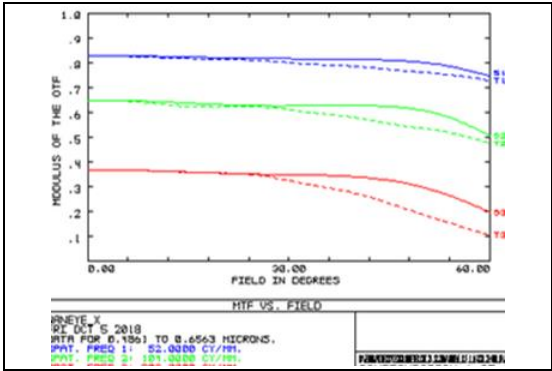
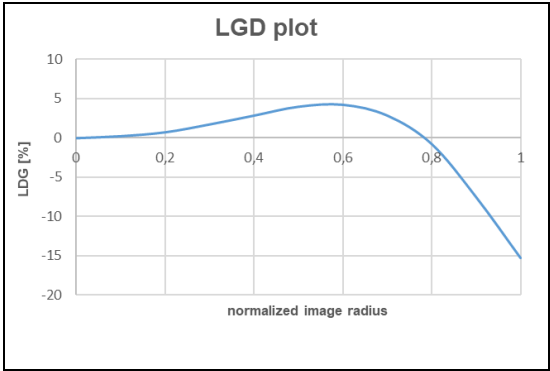


Figure 3: Distortion



- 1.4 Applications
- Medical applications
 - Endoscopy
 - Intraoral Scanning

2

Ordering information

Part number	Q number	Ordering code	Chroma	Package	Optics	Delivery form	Delivery quantity (MOQ)
508220013	Q65114A3385	NEM_RGB_2M_FOV120_F4.0	RGB	with 2 m cable	FOV120; F4	Spool	1
508220023	Q65114A3384	NEM_RGB_2.5M_FOV120_F4.0	RGB	with 2.5 m cable	FOV120; F4	Spool	1

i

Information:

The module device is mounted on a flat ribbon cable, measuring up to 2.5 m in length, that connects to the base station. However, if the customer requirements are discussed, it may be possible to assemble a slightly longer cable (up to 3 m).



Information:

Device traceability is based on the serial numbers labeled on the spools.



CAUTION:

The device is NOT supplied sterile! Medical use of the system, not integrated into a medical device, may lead to serious harm, illness, or death!



Attention:

The NanEyeM device, as is, was not made to be waterproof or liquid proof. It should be integrated in a tool or endoscope in such way the potting material, or adhesive, would seal all sides of the camera module, except the optical front window, from direct contact with water and/or liquids. Using the device without protection has a high potential to be damaged, like scratch the side wall painting, break the cable and even get water/liquids into it.

3 Pin assignment

3.1 Pin diagram

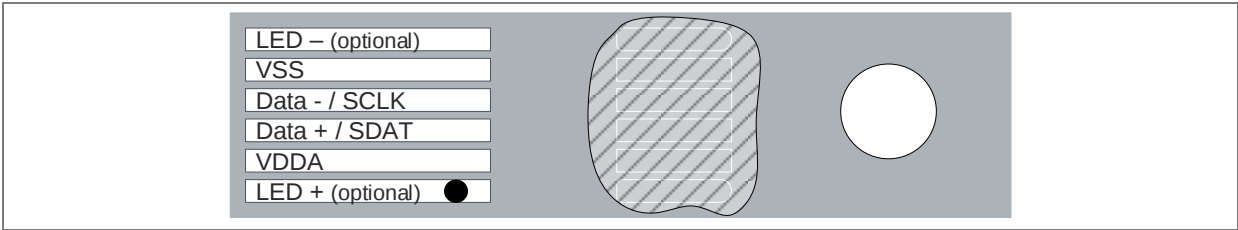
Table 4: Pin assignment module cable (Camera Front View)

	1	2	3	4
4-wire cable	VSS	SCLK / DATA-	SDAT / DATA+	VDDA

Figure 4: 4-wire cable pinout



Figure 5: 6-wire cable flexPCB connector pinout



3.2 Pin description

Table 5: Pin description of NanEyeM

Pin number		Pin name	Pin type ⁽¹⁾	Description
Cable 4-wire	Connector 6-wire			
	1	LED-	AO	LED cathode (optional) ⁽²⁾
1	2	VSS	VSS	Ground supply
2	3	SCLK / DATA-	DIO	Serial clock input, LVDS neg. output
3	4	SDAT / DATA+	DIO	Serial data input/output, LVDS pos. output
4	5	VDDA	Supply	Positive supply
	6	LED+	AI	LED anode (optional) ⁽²⁾

(1) Explanation of abbreviations:
DIO Digital Input/Output
AI Analog Input
AO Analog Output

(2) The current available NanEyeM products come with a 4-wire cable as in Figure 4. These connector pins are optional in case the user would like to connect to a LED device.

4 Absolute maximum ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under “Operating Conditions” is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 6: Absolute maximum ratings of NanEyeM

Symbol	Parameter	Min	Max	Unit	Comments
Electrical parameters					
V _{DDA}	Supply voltage to ground	-0.5	3.6	V	
V _{SCLK} , V _{SDAT}	Input pin voltage to ground	-0.5	3.6	V	
Electrostatic discharge					
ESD _{HBM}	Electrostatic discharge HBM	± 2		kV	JEDEC JS-001-2017
Temperature ranges and storage conditions					
T _A	Operating ambient temperature full module	15	55 ⁽¹⁾	°C	Full module incl. cable
	Silicon sensor only	0	70 ⁽¹⁾	°C	Good image quality 15 to 55 °C only
RH _{NC}	Relative humidity (non-condensing)	5	85 ⁽¹⁾	%	
T _{STRG}	Storage temperature range	-40	30	°C	See note ⁽²⁾
RH _{NC_STRG}	Long term storage humidity	0	60	%	
t _{STRG}	Storage time		3	years	
MSL _{M+CABLE}	Moisture sensitivity level Lens module with cable	N/A			Not applicable as only the cable gets soldered not the module

- (1) Long term exposure toward the maximum operating temperature will accelerate device degradation.
(2) UV curing process is in our conviction not causing any harm to the sensor.

5 Electrical characteristics

The parameters with Min and Max values are guaranteed with production tests or SQC (Statistical Quality Control) methods. Parameters without tolerance are typical values.

Table 7: Electrical characteristics of NanEyeM

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VDDA	Supply voltage		3.2	3.3	3.4	V
VN _{RMS} VDDA	RMS noise on VDDA				5	mV
VN _{PP} VDDA	Peak to peak noise on VDDA				20	mV
P _{CLK_STD} ⁽¹⁾	Internal pixel clock	set by mclk_mode [1:0] and high_speed[0]		1.03 2.05 4.09		MHz
P _{CLK_HS} ⁽²⁾	Internal pixel clock high speed	set by mclk_mode [1:0] and high_speed[0]		1.31 2.59 5.22		MHz
P _{tot_3.3}	Total power consumption	Idle mode = OFF, MCLK=31 MHz		12		mW
		Idle mode = ON		3.2		mW
Digital upstream interface						
V _{IL}	SCLK, SDAT low level input voltage		-0.3		0.4	V
V _{IH}	SCLK, SDAT high level input voltage		VDDA -0.3		VDDA +0.3	V
T _S	Setup time for upstream configuration relative to SCLK		3			ns
T _H	Hold time for upstream configuration relative to SCLK		3			ns
f _{SCLK_LVDS}	SCLK frequency in LVDS				2.5	MHz
LVDS downstream interface						
V _{CM}	Common mode output voltage (DATA+/-)		1	1.4	1.8	V
I _{DATA+,DATA-}	LVDS output signal current,	Set by output_curr[1:0]		600 ... 2000		μA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BCLK_STD	Bit clock for serial data transmission (12x Pclk)	Set by mclk_mode[1:0] and high_speed[0]		12 25 49		MHz
BCLK_HS	Bit clock for serial data transmission high speed (12x Pclk)	set by mclk_mode[1:0] and high_speed[0]		16 31 63		MHz
JDATA	Jitter data clock		-20		20	%
	LVDS differential peak-peak swing	Zterm=120Ω		72...240		mV
T _{slew, rising}	Output slew rate of rising edge			3		ns
T _{slew, falling}	Output slew rate of falling edge			3		ns

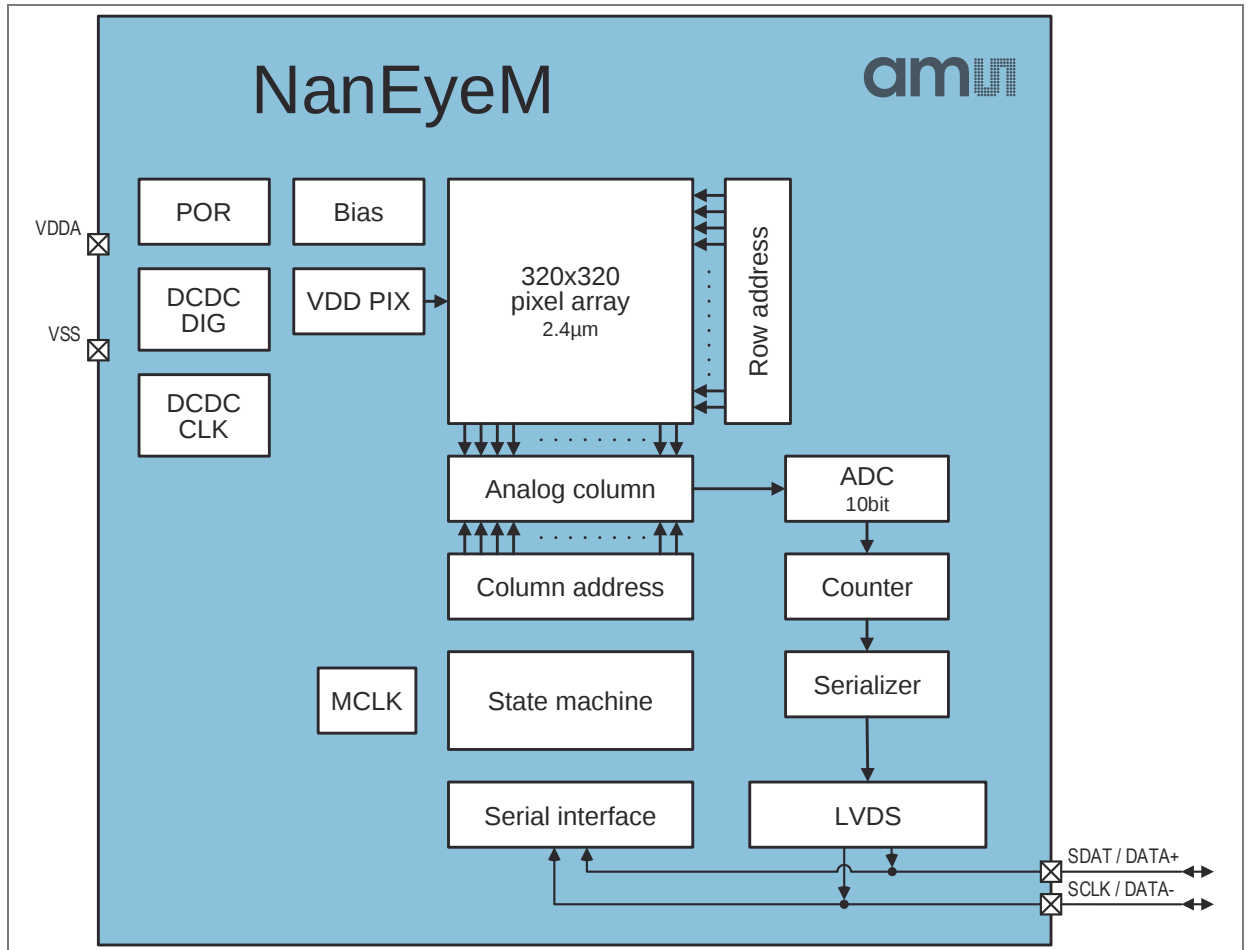
- (1) _STD -> assuming High Speed bit OFF
(2) _HS -> assuming HS Speed bit ON

6 Functional description

6.1 Sensor architecture

Figure 6 shows the image sensor architecture. The internal state machine generates the necessary signals for image acquisition. The image information received in the pixels (rolling shutter) is read out sequentially, row-by-row. On the pixel output, an analog gain is possible. The pixel values then passes to a column ADC cell, in which analog to digital conversion is performed. The digital signals are then read out over a LVDS.

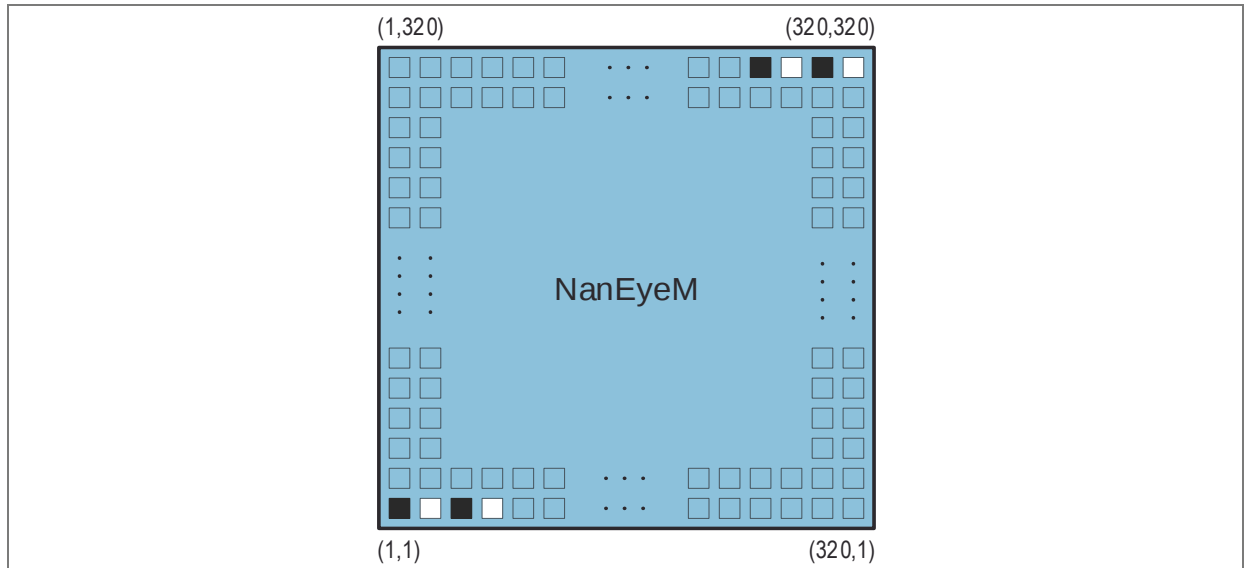
Figure 6: Functional blocks of NanEyeM



6.1.1 Pixel array

The pixel array consists of 320 x 320 square rolling shutter pixels with a pitch of 2.4 µm (2.4 µm x 2.4 µm). The pixel architecture used in this sensor is a 4T type structure, with two pixel vertically shared. This results in an optical area of 768 µm x 768 µm (1.09 mm diameter).

Figure 7: Pixel array



The pixels are designed to achieve maximum sensitivity with low noise (using CDS). Micro lenses are placed on top of the pixels for improved fill factor and quantum efficiency.

There are two electrical black pixels and two electrically saturated pixels on the upper right and lower left hand corner, which may be used to check consistency of received data.

Black pixel (1,1) can be used to compensate the black offset by subtraction it from the individual received pixel values.

6.1.2 Analog front end

The analog front end consists of 2 major parts, a column amplifier block and a column ADC block.

The column amplifier prepares the pixel signal for the column ADC. The column ADC converts the analog pixel value into a digital value. The architecture allows a full linear AD conversion of 10 bits, with a programmable conversion gain. All gain and offset settings can be programmed using the Single Ended Serial interface.

6.1.3 LVDS block

The LVDS block converts the digital data coming from the column ADC into standard serial LVDS data. During transfer of the image data, the pixel values are transmitted in bit serial manner with 12 bits and embedded clock using Manchester coding [start bit (1 bit) + data (10 bit) + stop bit (1 bit)]. The sensor has one LVDS output pair.

6.1.4 State machine

The state machine will generate all required control signals to operate the sensor. The clock is derived from an on-chip master clock generator (LVDS mode). The clock speed and so the number of transmitted frames can be set via registers bits. A detailed description of the registers and sensor programming can be found in chapter 6.4.2 and chapter 7 of this document.

6.1.5 Single ended serial interface

The single ended serial interface is used to load the registers with data. It is multiplexed with the LVDS interface, data can be sent in the frame windows of the receiving image information. The data in these registers is used by the state machine and ADC block while driving and reading out the image sensor. Features like exposure time, gain, offset and frame rate can be programmed using this interface. Chapter 6.4.2 and chapter 7 contain more details on register programming.

The sensor will start up in IDLE MODE, having the single ended serial interface active until the idle mode is deactivated.

6.1.6 Optics

The optional optics available for the sensor is a high performance miniature lens module. It will be directly mounted on the image sensor and has its best focus position defined by design, so no mechanical set of focus is needed. The front of the lens module is made of D 263®T eco clear borosilicate glass. The design is made in such a way that the surface towards the object is flat, so the lens performance is not influenced by the medium between the object and lens. Only the opening angle of the lens is reduced when the system operates in water.

6.2 Driving the NanEyeM

The NanEyeM image sensor is based on CMOS technology and is a system on chip, which means that all needed clocks and additional supplies are generated on-chip.

6.2.1 Supply voltage

The sensor operates from a single supply voltage VDDA. In addition, a VDDPIX (reset voltage for the pixels) as well as separated supplies for digital blocks are generated internally.

For reference schematic and external components please refer to chapter 8 Application information.

6.2.2 Start-up sequence

The sensor is fully self timed and operates in a free running master mode. After power up, the sensor performs an internal power on reset, and then moves to IDLE MODE, having the single ended serial upstream interface active. This gives the possibility to adjust the sensor settings, especially selecting the output mode, before disabling the idle mode and starting the image data transmission.

6.2.3 Reset sequence

No special reset sequence needed.

6.2.4 Frame rate

The frame rate can be adjusted by changing the settings for the master clock (MCLK). There is also a high speed mode available to generate even higher frame rates.

6.3 Matrix readout

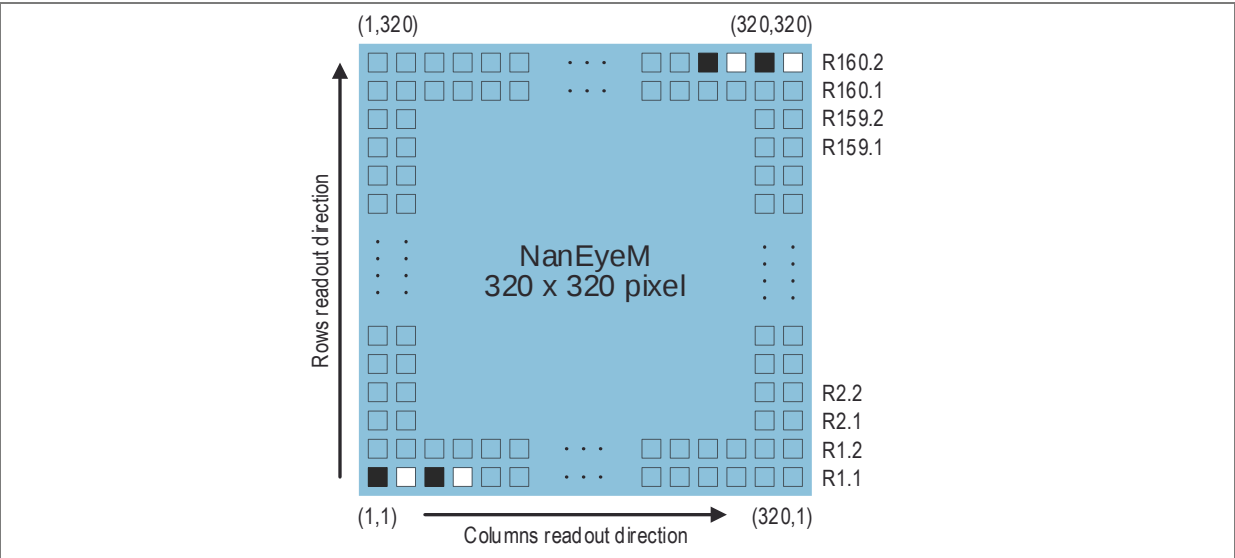
To guarantee a high fill factor a pixel layout with the two vertical electrical shared pixels has been developed.

The matrix readout is according to the following sequence:

- 1. Read first row (R1.1), starting in the position (1,1) and finishing in the position (1,320)
- 2. Read second row (R1.2), starting in the position (2,1) and finishing in the position (2,320)
- ...
- 3. Read last row (R160.2), starting in the position (320,1) and finishing in the position (320,320)

Note that (row,column), i.e., (2,1) represents row 2 column 1.

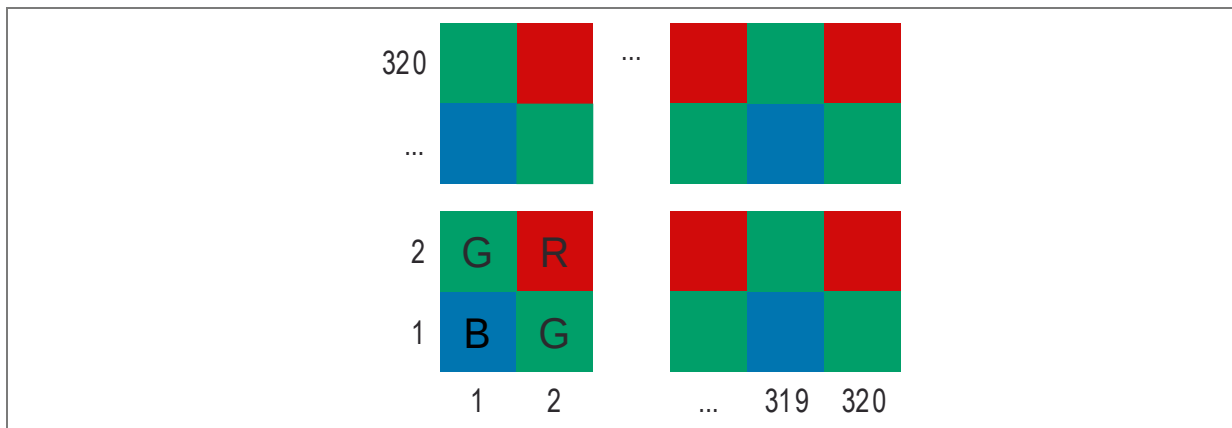
Figure 8: Shared pixel matrix readout



6.3.1 Color filters

The color filters used for NanEyeM are applied in a Bayer pattern. The first pixel read-out, pixel (1,1), is the bottom left one and has a blue filter.

Figure 9: Colored version bayer pattern matrix



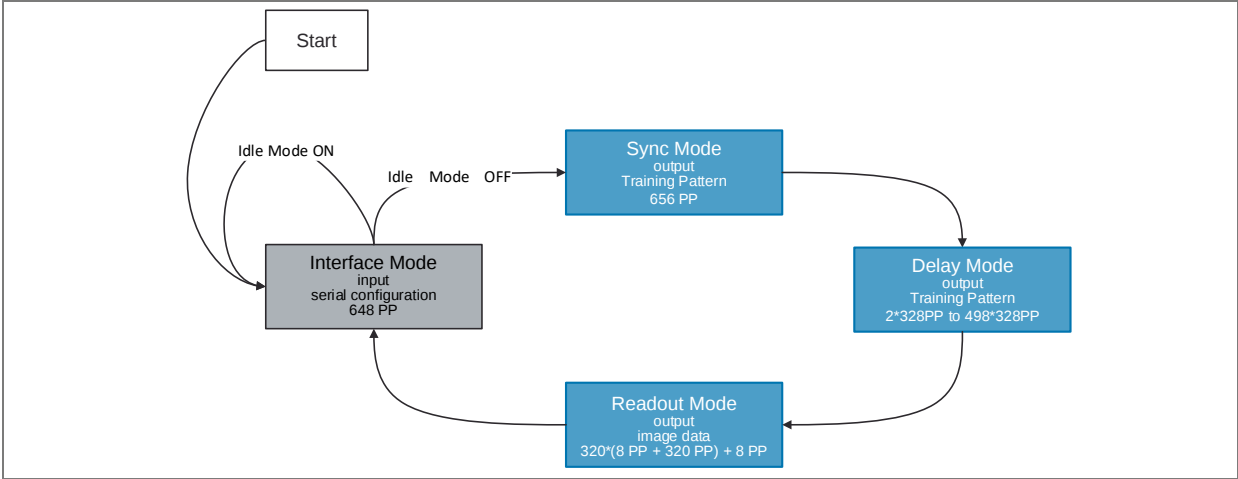
6.3.2 Sequence of operation

The NanEyeM sensor will start in INTERFACE MODE waiting for configuration and request to leave idle mode. After the request, the sensor will go to a loop of 4 modes, which are described below. The frame time is defined by the total duration of these 4 modes:

- **INTERFACE MODE:** during this mode, which is active during 648 PP (Pixel Period) it is possible to write and update the register configuration. In this mode DATA pins are used as SDAT and SCLK.
- **SYNC MODE:** during this mode the sensor is transmitting a training pattern to allow the sensor synchronization (duration of 656 PP).
- **DELAY MODE:** during this mode the sensor will keep the previous state during the programmed time while sending the sync pattern. The time can be programmed between 2 to 498 row periods.
- **READOUT MODE:** during this mode the sensor assumes that the synchronization is done and starts to send image data, the pixel values are transmitted in bit serial manner over an LVDS channel with embedded clock, or single ended depending on the selected transmission mode. Note that before each row a Start of Row identification is sent with the duration of 8 PP and that after the last row an End Of Frame is sent with the duration of 8 PP.

The sensor transmits a synchronization pattern at least for the period of four rows, corresponding to the SYNC MODE and to the DELAY MODE (if set to the minimum programmable value). But it can transmit the pattern continuously for a longer time period, according the rows_delay[4:0] value programmed, which can take from 2 to 498 row clock period (2*328PP to 498*328PP).

Figure 10: Sequence of operation



(1) PP stands for Pixel Period, which is the time equivalent of a transmission of 12 bits.

Table 8: Matrix readout sequence

Phase #	Status	Start bit	Data XOR	Interface status	Duration	Function
INTERFACE MODE						
SERIAL	Time for serial configuration ⁽¹⁾	N/A	N/A	S_INT IN	648 PP ⁽²⁾	Serial Interface
SYNC MODE						
SYNC	Transmission of continuous 0	0	Yes	LVDS OUT	328*2 PP	Re-Synchronization
DELAY MODE						
DELAY	Transmission of continuous 0	0	Yes	LVDS OUT	328*2 PP to 328*498 PP	Programmed Delay
READOUT MODE						
RD R1.1	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 1)
RD R1.2	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 2)
RD R2.1	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 3)

Phase #	Status	Start bit	Data XOR	Interface status	Duration	Function
RD R2.2	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 4)
readout other rows						
RD R160.1	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 319)
RD R160.2	Transmission of continuous 0	0	Yes	LVDS OUT	8 PP	Start of Row
	Transmission of 320 pixel values	1	Yes	LVDS OUT	320 PP	Image Data (Row 320)
RD EOF	Transmission of continuous 0	0	No	LVDS OUT	8 PP	End of Frame

- (1) It is recommended to drive the data bus during the entire upstream communication phase, even if no register data is sent to the sensor. This is to avoid pick up of EMI on the lines floating during the communication phase when not driven by the application.
- (2) When IDLE MODE is OFF. If IDLE MODE is enabled the sensor remains in this working mode until the IDLE MODE is disabled.



CAUTION:

1. The sensor is fully self-timed and cycles between the downstream and the upstream mode. Therefore, it is the user's responsibility to tristate the upstream drivers of the serial configuration link prior to the start of data transmission from the sensor.
2. Due to the limited current output from the sensor, it is not expected that conflicting drive of the data lines will permanently destroy the sensor, however this condition would seriously degrade the data integrity and is not qualified in terms of device reliability and lifetime.



Information:

Please note that the first frame after power on, or after idle mode deactivation, should be discarded, due to a wrong exposure.

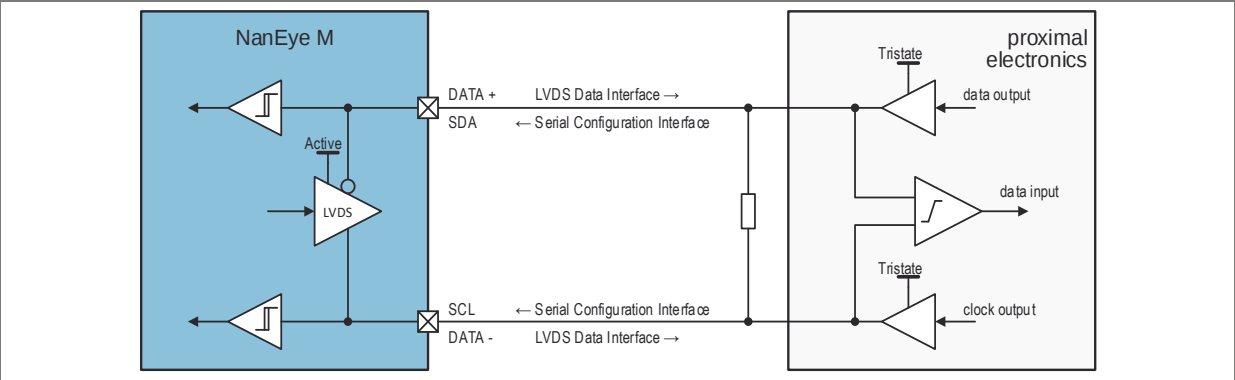
6.4 Serial interface

The chip features a bi-directional data interface. During transfer of the image data, the pixel values are transmitted in bit serial manner over an LVDS channel with an embedded clock. After each frame, the data interface is switched for a defined time to an upstream configuration interface. This needs synchronization every time it passes from the upstream to a new downstream mode at the image receiver side. The positive LVDS channel holds the serial configuration data, and the negative channel holds the serial interface clock.

By register configuration the downstream interface can be chosen to be LVDS type with the serial data EXOR combined with the bit clock (Manchester Code).

For any application where the sensor is used with connection cable between the sensor and the receiver, the use of the LVDS mode is recommended.

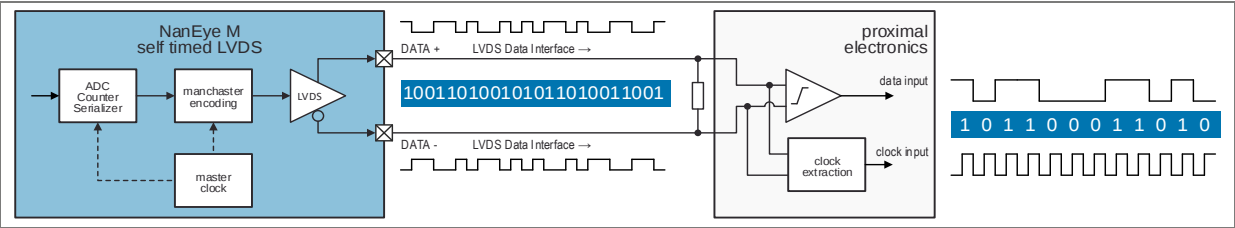
Figure 11: Data interface between sensor and proximal electronics



6.4.1 NanEyeM LVDS data interface (Downstream)

The NanEyeM image data on chip is generated as a 10-bit representation. A start and a stop bit are then added to the data. The bit serial data interface then transmits the data with 12 times the pixel frequency.

Figure 12: LVDS downstream mode



6.4.1.1 Data word

The data word is EXOR gated with the serial clock before sent bit serial according to the following scheme:

Table 9: Data word encoding

Bit #	0	1	2	3	4	5	6	7	8	9	10	11
Function	Start	Pixel Data (10 bits)										Stop
Content	1	MSB										LSB 0

An example of this is:

- 10-bit data word: 0110001101
- Including start and stop bits: 101100011010
- 12-bit word EXOR with the data clock:
 - 01 01 01 01 01 01 01 01 01 01 01 01 - data clock (main clock)
 - 11 00 11 11 00 00 00 11 11 00 11 00 - 12-bit data @ data clock frequency
 - 10 01 10 10 01 01 01 10 10 01 10 01 - data word result

Please note that the stop bit is missing in the last pixel data word (320, 320). Therefore, taking in consideration the previous example, the result would be the following:

- Including only the start bit for a 11-bit word: 10110001101
- 11-bit word EXOR with the data clock, plus Start bit of End of Frame (Not EXOR)
 - 01 01 01 01 01 01 01 01 01 01 01 - data clock (main clock) |
 - 11 00 11 11 00 00 00 11 11 00 11 - 11-bit data @ data clock frequency
 - 10 01 10 10 01 01 01 10 10 01 10 - data word result

6.4.1.2 Training pattern word

The training pattern is transmitted during SYNC MODE and DELAY MODE, and also during READOUT MODE as Start of Row identification. It is a 12-bit word with all 0's, start and stop bit also at 0, EXOR gated with the main clock.

Table 10: Training pattern word encoding

Bit #	0	1	2	3	4	5	6	7	8	9	10	11
Function	Start	Start Row										Stop
Content	0	0	0	0	0	0	0	0	0	0	0	0

An example of this is:

- 10-bit data word: 0000000000
- Including start and stop bits: 000000000000
- 12-bit word EXOR with the data clock:
 - 01 01 01 01 01 01 01 01 01 01 01 01 - data clock (main clock)
 - 00 00 00 00 00 00 00 00 00 00 00 00 – 12-bit at 0's @ data clock frequency
 - 01 01 01 01 01 01 01 01 01 01 01 01 – training pattern word result

6.4.1.3 End of frame word

The end of frame word is similar to the training pattern, it is a 12-bit word with all 0's, start and stop bit also at 0, but in this particular case it is not EXOR with main clock. It is transmitted in the end of the readout phase (READOUT MODE).

Table 11: End of frame word encoding⁽¹⁾

Bit #	0	1	2	3	4	5	6	7	8	9	10	11
Function	Start	Start Row										Stop
Content	0	0	0	0	0	0	0	0	0	0	0	0

(1) No EXOR with main clock!

An example of this is:

- 10-bit data word: 0000000000
- Including start and stop bits: 000000000000
- 12-bit word **no** EXOR with the data clock:
 - 01 01 01 01 01 01 01 01 01 01 01 01 – data clock (main clock)
 - 00 00 00 00 00 00 00 00 00 00 00 00 – 12-bit at 0's @ data clock frequency
 - 00 00 00 00 00 00 00 00 00 00 00 00 – end of frame word result

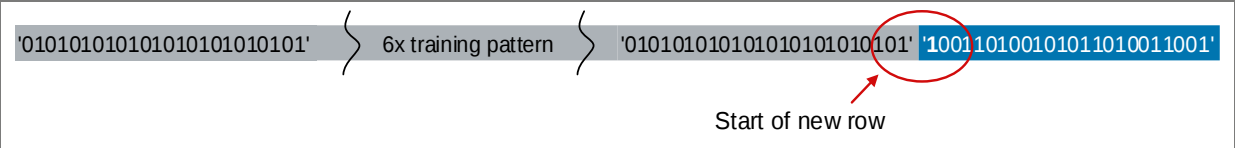
6.4.1.4 Start of row identification

Note that the start of row identification consists in sending the training pattern (01010101010101010101) 8 times.

After 8 times transmitting the training pattern the data transmission for a particular row starts. Note that is possible to identify a new row easily by detecting two ones after the eight training

pattern words. The ones appearance results from the last bit of the start line and the first bit of the image data (start bit XOR with data clock) as is shown below:

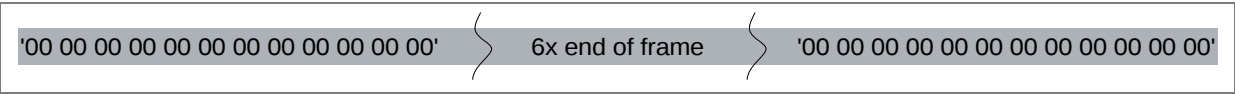
Figure 13: Start of row identification



6.4.1.5 End of frame identification

The End of Frame identification is sent after the last row and before the Serial Phase, it is the End of Frame word repeated 8 times.

Figure 14: End of frame identification



6.4.1.6 Re-sync identification

The Re-sync identification is sent during the SYNC MODE after the INTERFACE MODE (serial upstream configuration phase) in order to restart the sensor synchronism. It will send the training pattern word during 656 PP.

6.4.1.7 DELAY MODE identification

During DELAY MODE the training word is sent 2*328 to 498*328 times. The number of repetitions can be programmed with rows_delay[4:0].

6.4.2 Serial configuration interface (Upstream)

The serial interface is active for 648 PP (INTERFACE MODE) and consists of two 16-bit write only registers. The registers can be updated between frames by the serial data line (SDAT) and by the serial clock line (SCLK) external controlled signal. The registers are written by

sending a 4-bit update code, followed by a 3-bit register address (only register 000 and 001 are implemented), 16-bit register data and a bit fixed to “0”.

Sending data to the sensor must not be done with the first clock pulse provided to the sensor. It is required to send at least one activation clock pulse upfront. It needs to be avoided to send configuration data in the last PP of the INTERFACE MODE.

All data is written MSB to LSB. Data is captured on the rising edge of SCLK. It is recommended to change SDAT on the falling edge of SCLK to guarantee maximum set-up and hold times.

The content of the input shift register is updated to the effective register once a correct update code (1001) has been received and shifted by 24 serial clocks. The input shift register is reset to all 0's, 1 SCLK clock after the code detection.

The below table indicates the sequence of writing update code, register address and register data.

Table 12: Register update sequence

# Rising edge of SCL after reset	1	2	3	4	5	6	7	8	9	...	22	23	24
Function	Update Code				Register Address ⁽¹⁾			Register Content (16-bit)					Reset
Content	1	0	0	1	0	0	X	MSB				LSB	0

(1) Register address 000 for Configuration_0 register
Register address 001 for Configuration_1 register

- A correct sequence must have 24 SCLK, where:
- The first 4 SCLK are for detection of a correct code (must be 1001).
 - The next 3 SCLK will indicate the register to be written (000 or 001).
 - The next 16 SCLK will pass the data information (from MSB to LSB).
 - Finally, the last SCLK will pass the bit “0” that is used to separate words.

To signalize the end of the INTERFACE MODE, the device transmits a specific word in the last PP:

- LVDS: 00 00 00 00 00 00 00 01 01 01 01 01

6.5 Sensor programming

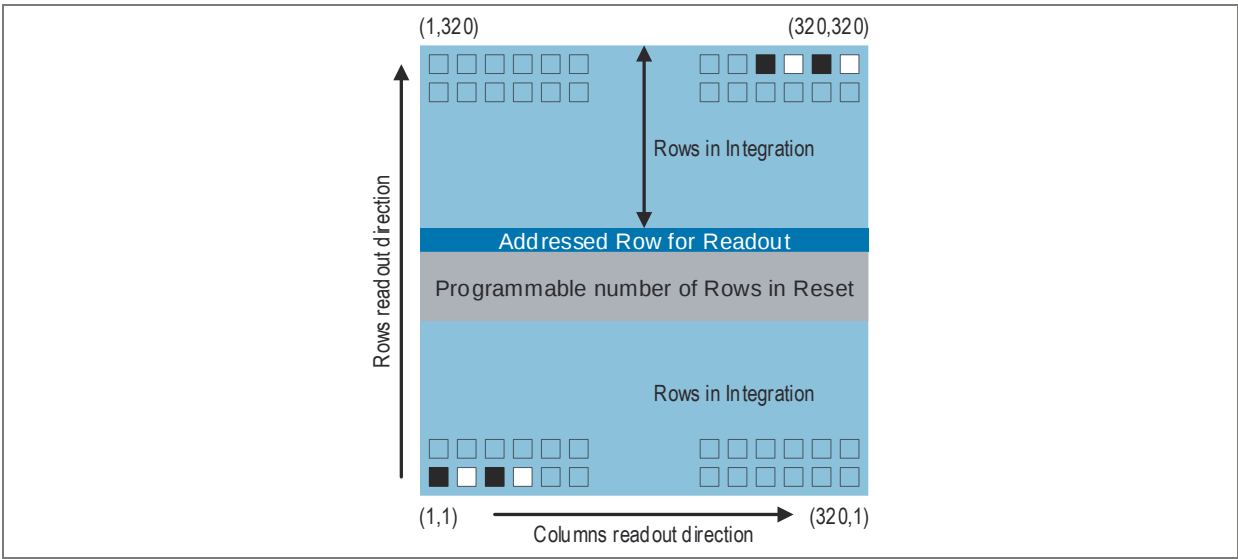
This section explains how the NanEyeM can be programmed using the on-board registers.

6.5.1 Exposure time control

Exposure time is defined based on the amount of rows in reset set by user and the frame rate, which is dependent on the main clock frequency and the delay mode setting. The NanEyeM sensor features a rolling shutter, which means one row is selected for readout while a defined number of previous rows are in reset, and all the other rows are in integration.

Configuring the DELAY MODE at the beginning of each frame can be used to increase the integration time.

Figure 15: Row readout operation



The frame time is defined by a full cycle in the state-machine including the matrix readout as well as the time between frames for INTERFACE, SYNC and DELAY MODE.

Equation 1:Frame time

$$t_{frame} = t_{rows_btw_frame} + t_{rows_matrix}$$

The effective exposure time thus is given by the formula:

Equation 2:Exposure time

$$t_{exp} = t_{rows_btw_frame} + t_{rows_matrix} - t_{rows_in_reset} - t_{rows_in_readout}$$

t_{exp} = The effective exposure time
 $t_{rows_btw_frames}$ = Time for of rows between frames
 t_{rows_matrix} = Time for active pixel matrix readout
 $t_{rows_in_reset}$ = Time of rows in reset
 $t_{rows_in_readout}$ = Time of rows in readout

Equation 3:Time for rows between frame

$$t_{rows_btw_frame} = t_{rows_spi} + t_{rows_sync} + t_{rows_delay}$$

$$t_{rows_spi} = 648 \text{ PP}$$

$$t_{rows_sync} = 2 * 328 \text{ PP} = 656 \text{ PP}$$

$$t_{rows_delay} = (16 * rows_delay[4:0] + 2) * 328 \text{ PP}$$

Equation 4:Time for active pixel matrix readout

$$t_{rows_matrix} = 320 * 328 \text{ PP} + 8 \text{ PP} = 104968 \text{ PP}$$

Determined by the size of the pixel matrix with 328 PP per each row.

Equation 5:Time for rows in reset

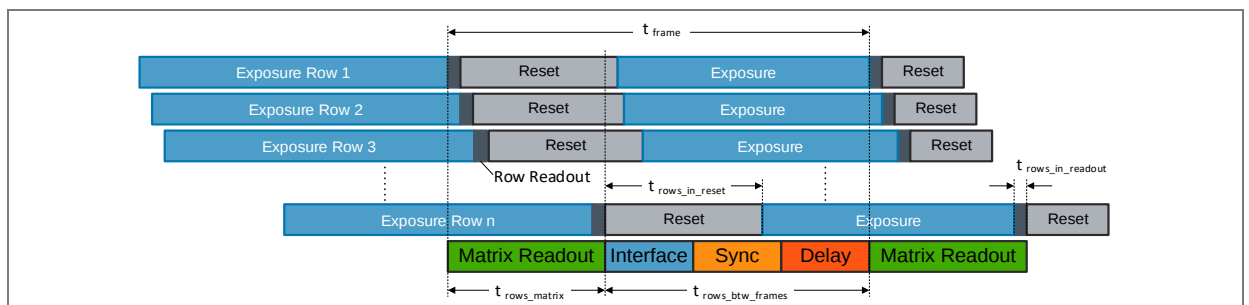
$$t_{rows_in_reset} = (2 * rows_in_reset[7:0] + 2) * 328 \text{ PP}$$

$rows_in_reset[7:0]$ maximum value is equal to the total number of sensor rows.

Equation 6:Time for row in readout

$$T_{rows_in_readout} = 2 * 328 \text{ PP} = 656 \text{ PP}$$

Figure 16: Row readout timing diagram



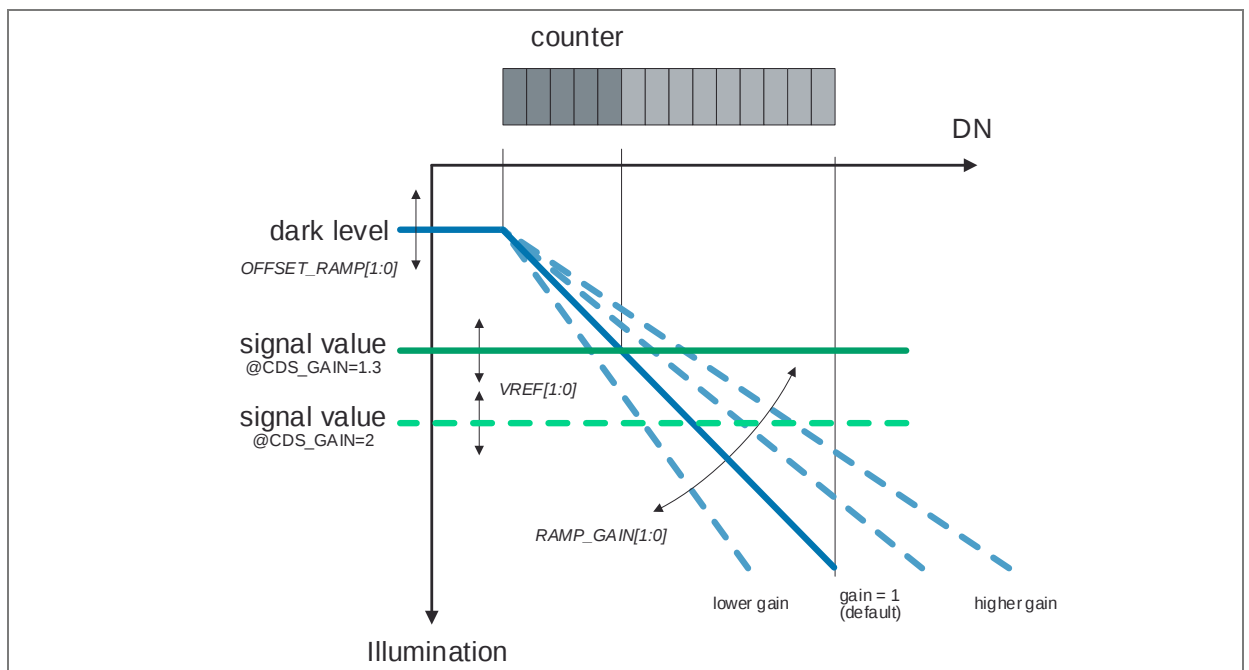
6.5.2 Offset and analog gain

It is a 10-bit full linear ADC. The architecture of the ADC allows programming several parameters:

- Voltage Reference for signal (vref[1:0])
- Ramp Gain (ramp_gain[1:0])
- Ramp Offset Voltage (offset_ramp[1:0])
- CDS gain (cds_gain[0])
- CDS current (bias_curr_increase[0])

See the configurable values in 7 Register description.

Figure 17: ADC settings



7 Register description

7.1 Detailed register description

Table 13: Configuration_0 register

Addr: 00h		Configuration_0		
Bit	Bit name	Default	Access	Bit description
15:8	rows_in_reset[7:0]	80h	WO	Sets the number of rows in reset: $rows_{in_rst} = 2 * rows_in_reset[7:0] + 2$ Default: 258
7:6	vrst_pix[1:0]	10b	WO	Sets the pixel reset voltage: 0: 2.2 V 1: 2.4 V 2: 2.6 V (recommended)⁽¹⁾ 3: 2.8 V
5:4	ramp_gain[1:0]	01b	WO	Sets the analogue ADC ramp gain: See Table 14
3:2	offset_ramp[1:0]	01b	WO	Sets the ramp offset (dark level) value 0: 1.9 V 1: 2 V 2: 2.1 V 3: 2.2 V (recommended) ⁽²⁾
1:0	output_curr[1:0]	01b	WO	Sets the LVDS output current 0: 600 μ A 1: 1200 μA 2: 1800 μ A 3: 2000 μ A

- (1) For best performance, use this value. It is not recommended to change.
- (2) It is recommended that offset_ramp[1:0] voltage to be always 0.1 V higher than vref[1:0] voltage, to guarantee the highest dynamic range, avoiding that the sensor does clips in dark.

Table 14: ADC ramp gain settings

MCLK [MHz]	ramp_gain[1:0]	Ramp gain	MCLK [MHz]	ramp_gain[1:0]	Ramp gain
12	00	0.79	16	00	0.79
	01	0.99		01	0.99
	10	1.32		10	1.32
	11	1.97		11	1.97

MCLK [MHz]	ramp_gain[1:0]	Ramp gain	MCLK [MHz]	ramp_gain[1:0]	Ramp gain
25	00	0.80	31	00	0.81
	01	1.00		01	1.01
	10	1.33		10	1.35
	11	2.00		11	2.03
49	00	0.83	63	00	0.83
	01	1.03		01	1.04
	10	1.38		10	1.39
	11	2.07		11	2.10

Table 15: Configuration_1 register

Addr: 01h		Configuration_1			
Bit	Bit name	Default	Access	Bit description	
15:11	rows_delay[4:0]	00h	WO	Sets the number of rows period in delay mode $rows_{delay} = 16 * rows_delay[4:0] + 2$ Default: 2	
10	bias_curr_increase[0]	0b	WO	0: Nominal bias current 1: ~2x bias current, reduces settling time for high speed applications	
9	cds_gain[0]	1b	WO	0: CDS gain 1.3 (recommended) 1: CDS gain 2	
8	output_mode[0]	1b	WO	0: Do not use 1: LVDS	
7:6	mclk_mode[1:0]	01b	WO	Sets main clock frequency: See Table 16 0: Main clock 2x 1: Default 2: Main clock /2 3: Main clock /2	
5:4	vref[1:0]	01b	WO	Sets the reference voltage for CDS: 0: 1.9 V 1: 2 V 2: 2.1 V (recommended) ⁽¹⁾ 3: 2.2 V	
3:2	cvc_curr[1:0]	10b	WO	Sets the CVC current: See Table 17. Recommended to set to 01b.	
1	idle_mode[0]	1b	WO	Sets the sensor to work in idle mode with lower power consumption 0: Idle mode disabled 1: Idle mode enabled	
0	high_speed[0]	0b	WO	Sets clock to high speed mode: See Table 16.	

Addr: 01h		Configuration_1			
Bit	Bit name	Default	Access	Bit description	
				0: MCLK high speed mode off 1: MCLK high speed mode enabled	

(1) It is recommended that vref[1:0] voltage to be always 0.1 V lower than offset_ramp[1:0] voltage, to guarantee the highest dynamic range, avoiding that the sensor does clips in dark.

Table 16: Main clock configurations & frame rates

high_speed[0]	mclk_mode[1:0]	Description	Interface speed MCLK [MHz]	Frame rate [fps]
0	00	Main clock 2x	49.1	38
	01	Default	24.7	19
	1x	Main clock /2	12.3	9
1	00	Main clock 2x	62.6	49
	01	Default HS	31.1	24
	1x	Main clock /2	15.7	12

Table 17: CVC current settings

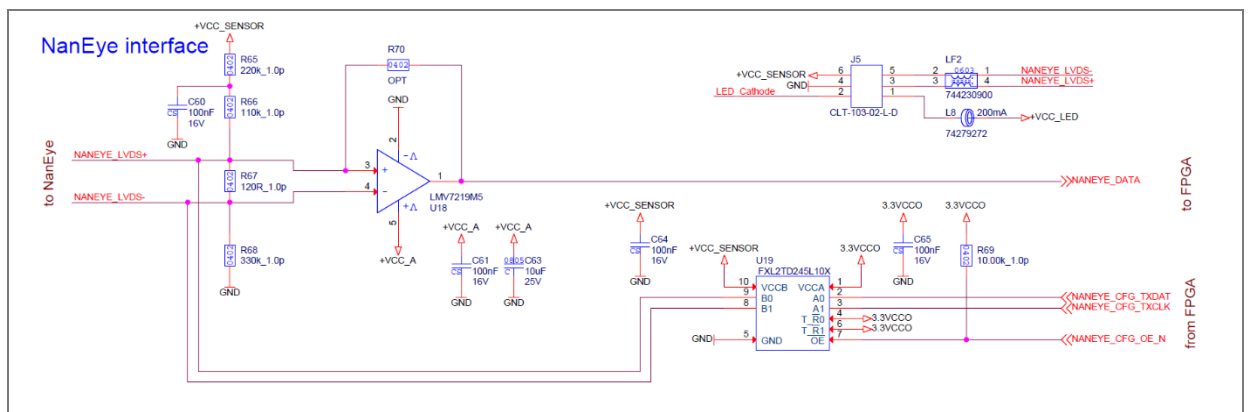
MCLK [MHz]	CVC_CURR[1:0]	CVC current [µA]	MCLK [MHz]	CVC_CURR[1:0]	CVC current [µA]
12	00	0.36	16	00	0.46
	01	0.79		01	1.03
	10	0.98		10	1.29
	11	1.44		11	1.88
25	00	0.69	31	00	0.90
	01	1.58		01	2.05
	10	1.98		10	2.59
	11	2.93		11	3.85
49	00	1.54	63	00	1.75
	01	3.18		01	4.14
	10	4.06		10	5.30
	11	6.07		11	7.95

8 Application information

8.1 Recommended LVDS receiver electronics

The direct interface of the LVDS data to an FPGA or DSP differential input is not guaranteed. It is recommended to use a LVDS detections circuit based on a fast comparator, which fixes the LVDS signals common mode.

Figure 18: NanEyeM interface schematic (for information only)



In order to increase the robustness of the de-serialization under the presence of significant jitter, which should be expected from the on-chip oscillator, the data is EXOR combined with the data clock.

To reliably de serialize the incoming data, the receiver side should sample the data at least with 750 MHz ($> 10\times$ of the MCLK frequency) to properly detect the phase of the transitions.

When defining the drive strength of the upstream drivers in the proximal circuitry it has to be considered that the serial clock and the serial data will couple to each other over the bit lines termination resistor. To reduce noise coupling to the analog electronics the LVDS output current is configured between 600 μ A to 2 mA (by serial interface), which will guarantee a save detection and de-serialization based on very low voltage swing LVDS receiver.

Driving the serial configuration data should be carefully designed along with the cables inductance to avoid signal overshoot at the chip side. It is recommended to use slew rate-controlled drivers with a low slew rate. No distal termination of the data lines is implemented on chip.

8.2 Supply generation

Having an LDO to generate a dedicated low noise supply is recommended. It has to be kept in mind that the cable is about 7 Ω per meter length. So, for different cable length and clock speeds used it should be verified that the supply voltage at the sensor is within the required range.

8.3 External components

Figure 19: External components LVDS

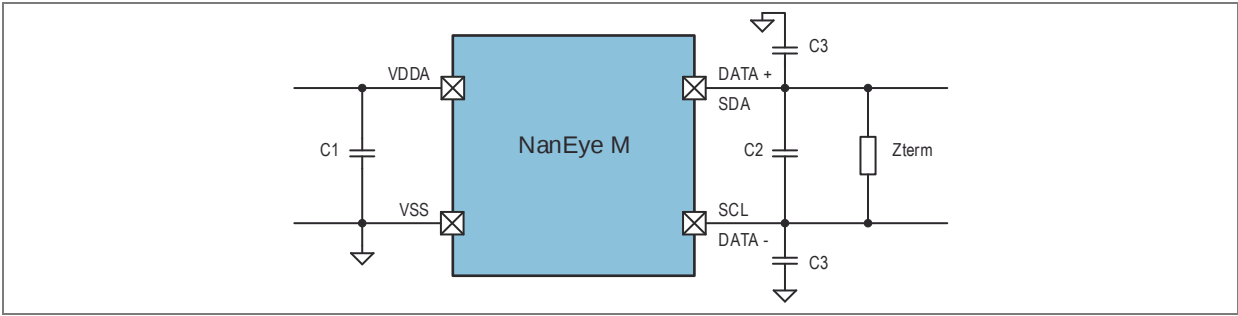
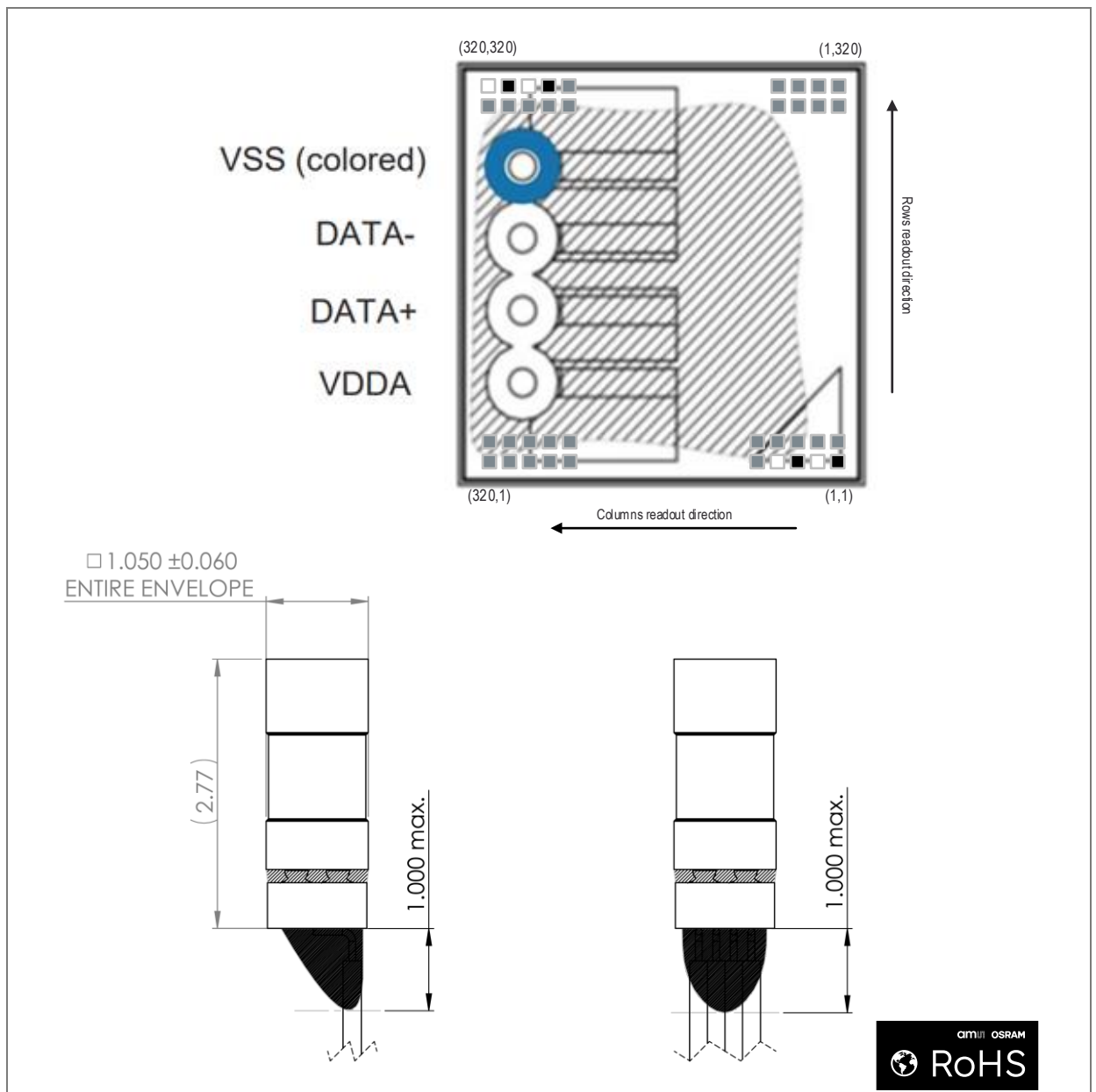


Table 18: External components recommendations

Component	Description	Nominal value	Unit
C1	Power supply decoupling (host system board)	>100	nF
C2	Differential load on LVDS lines (parasitics)	<3	pF
C3	Single ended load on LVDS lines (parasitics)	<5	pF
Zterm	Impedance of LVDS termination	120	Ω

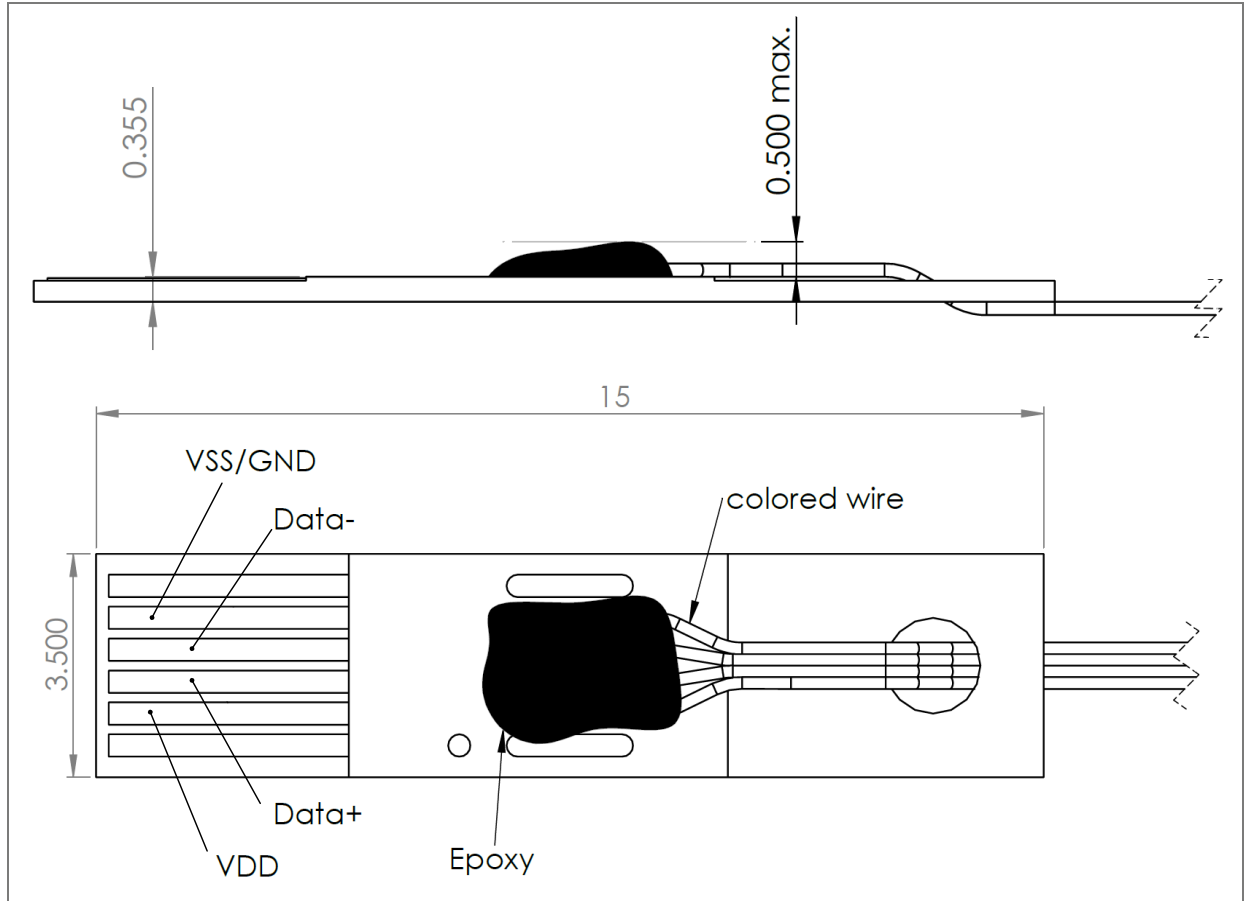
9 Package drawings & markings

Figure 20: NanEyeM with lens and cable soldered (bended) package outline drawing⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾⁽⁵⁾



- (1) All dimensions are in millimeters. Angles in degrees.
- (2) If not otherwise noted all tolerances are ± 0.1 mm.
- (3) This package contains no lead (Pb).
- (4) The pixels shown in the drawing are for information only. Its dimensions are not up to scale, as well as its positions are not precisely aligned with the chip.
- (5) This drawing is subject to change without notice.

Figure 21: NanEyeM flexPCB connector



- (1) All dimensions are in millimeters. Angles in degrees.
- (2) If not otherwise noted all tolerances are ± 0.1 mm.
- (3) This package contains no lead (Pb).
- (4) This drawing is subject to change without notice.

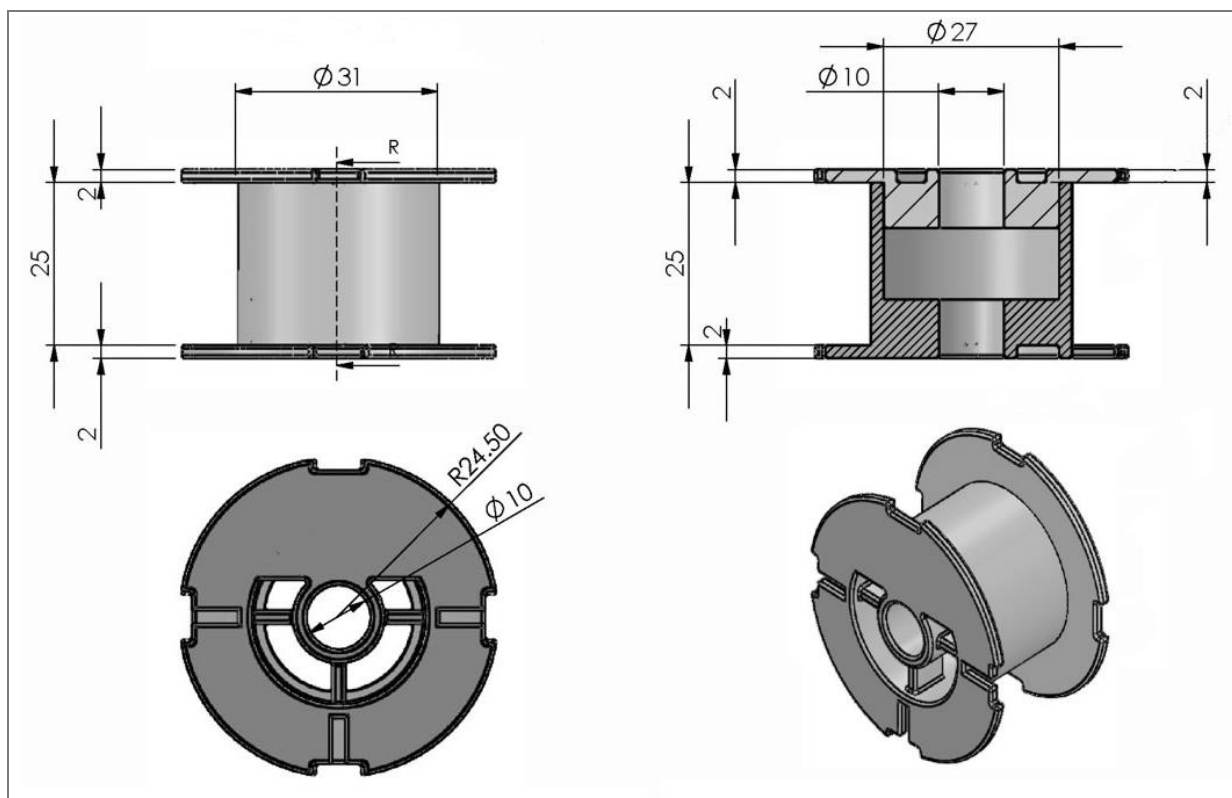


Information:

The NanEyeM mating connector (receptacle) part number is 06FLT-SM2-TB(LF)(SN).

10 Tape & reel information

Figure 22: Spool dimensions for module plus cable shipments⁽¹⁾⁽²⁾⁽³⁾



- (1) All dimensions are in millimeters. Angles in degrees.
- (2) If not otherwise noted all tolerances are ± 0.1 mm.
- (3) This drawing is subject to change without notice.

11 Appendix

11.1 Evaluation system

Optionally with the NanEyeM module, ams OSRAM provides a base station and software to run the device on a PC in real-time with all necessary image corrections. The complete system consists of the module, the USB interface box and the PC software. For more information, please check ams OSRAM [webpage](#).

12 Revision information

Document status	Product status	Definition
Product Preview	Pre-development	Information in this datasheet is based on product ideas in the planning phase of development. All specifications are design goals without any warranty and are subject to change without notice
Preliminary Datasheet	Pre-production	Information in this datasheet is based on products in the design, validation or qualification phase of development. The performance and parameters shown in this document are preliminary without any warranty and are subject to change without notice
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Changes from previous released version to current revision v3-00	Page
Document contents were transferred to new ams OSRAM datasheet template	
Key Specification table moved to Section 1	4-5
Updated Key Benefits & Features table	5
Electro-Optical Characteristics Info moved to Section 1	6-7
Added Q numbers	7
Block Diagram moved to Section 6	13
Added info about first frame	20
Added info about last pixel missing stop bit	22
Register Setting Vrst_pix maximum voltage value correction	29
Added info about pixel position relative to the footprint	34
Corrected typo on connector mechanical drawing	35
Added info about NanEyeM connector receptable	35

- Page and figure numbers for the previous version may differ from page and figure numbers in the current revision.
- Correction of typographical errors is not explicitly mentioned.

13 Legal information

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